

P/N: L-53F3BT

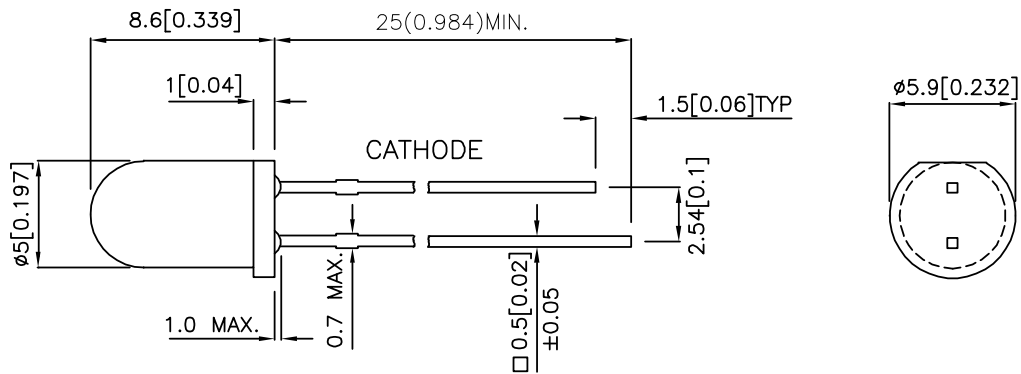
Features

- MECHANICALLY AND SPECTRALLY MATCHED TO THE PHOTOTRANSISTOR.
- BLUE TRANSPARENT LENS .
- RoHS COMPLIANT.

Description

F3 Made with Gallium Arsenide Infrared Emitting diodes.

Package Dimensions



Notes:

1. All dimensions are in millimeters (inches).
2. Tolerance is ± 0.25 (0.01") unless otherwise noted.
3. Lead spacing is measured where the leads emerge from the package.
4. Specifications are subject to change without notice.

Selection Guide

Part No.	Dice	Lens Type	Po (mW/sr) [2] @ 20mA*50mA		Viewing Angle [1]
			Min.	Typ.	2θ1/2
L-53F3BT	GaAs	BLUE TRANSPARENT	4	20	30°
			*7	*30	

Notes:

1. θ1/2 is the angle from optical centerline where the luminous intensity is 1/2 the optical centerline value.
2. * Luminous intensity with asterisk is measured at 50mA. Radiant intensity / luminous flux: +/-15%.

Electrical / Optical Characteristics at TA=25°C

Item	P/N	Symbol	Typ.	Max.	Units	Test Conditions
Forward Voltage[1]	F3	V _F	1.2	1.6	V	I _F =20mA
Reverse Current	F3	I _R	-	10	uA	V _R =5V
Capacitance	F3	C	90	-	pF	V _F =0V;f=1MHz
Peak Spectral Wavelength	F3	λ _P	940	-	nm	I _F =20mA
Spectral Bandwidth	F3	Δλ _{1/2}	50	-	nm	I _F =20mA

Note:

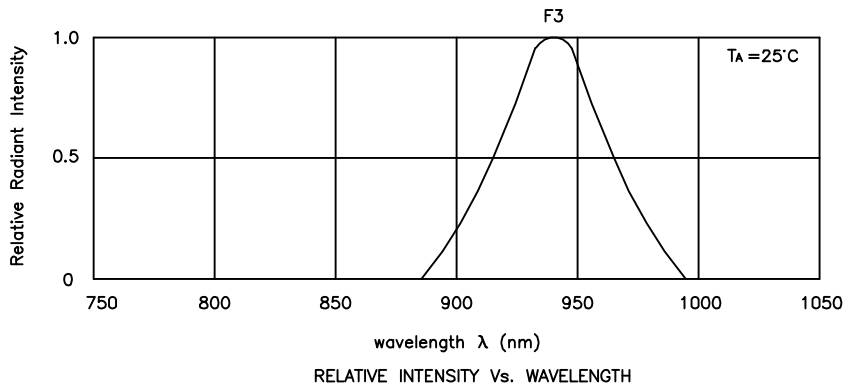
1. Forward Voltage: +/-0.1V

Absolute Maximum Ratings at TA=25°C

Parameter	Symbol	F3	Units
Power Dissipation	P _T	100	mW
DC Forward Current	I _F	50	mA
Peak Forward Current[1]	i _{FS}	1.2	A
Reverse Voltage	V _R	5	V
Operating Temperature	T _A	-40 To +85	°C
Storage Temperature	T _{STG}	-40 To +85	°C
Lead Solder Temperature [2]	260°C For 3 Seconds		
Lead Solder Temperature [3]	260°C For 5 Seconds		

Notes:

1. 1/100 Duty Cycle, 10us Pulse Width.
2. 2mm below package base.
3. 5mm below package base.



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